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# **SBA-4086(Z)**

# DCto5GHz, CASCADABLE InGaP/GaAs HBT

**MMIC AMPLIFIER** 

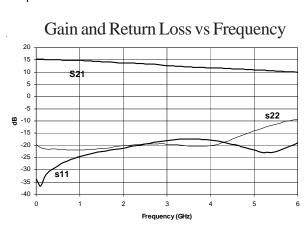


RoHS Compliant and Pb-Free Product (Z Part Number) Package: SOT-86

### **Product Description**

RFMD's SBA-4086 is a high performance InGaP/GaAs Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration designed with InGaP process technology provides broadband performance up to 5GHz with excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only a single positive supply voltage, DCblocking capacitors, a bias resistor, and an optional RF choke are required for operation.





#### **Features**

- IP3=33.5dBm at 1950MHz
- P<sub>OUT</sub>=12.3dBm at -45dBc ACP IS-95 1950 MHz
- Robust 1000V ESD. Class 1C
- Operates From Single Supply
- Patented Thermal Design

## **Applications**

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite **Terminals**

Parameter	Specification			Unit	Condition	
raiailletei	Min.	n. Typ. Max.		UIIIL	Condition	
Small Signal Gain	13.3	14.8	16.3	dB	850MHz	
	12.7	14.2	15.7	dB	1950MHz	
Output Power at 1dB Compression		19.1		dBm	850MHz	
	17.5	19.0		dBm	1950MHz	
Output Third Order Intercept Point		36.5		dBm	850MHz	
	31.5	33.5		dBm	1950MHz	
Output Power		12.3		dBm	1950 MHz, -45 dBc ACP IS-95 9 Forward Channels	
Bandwidth		5000		MHz	Return Loss>10dB	
Input Return Loss	14.0	21.0		dB	1950MHz	
Output Return Loss	14.0	20.5		dB	1950MHz	
Noise Figure		4.8	5.8	dB	1950MHz	
Device Operating Voltage	4.6	5.0	5.4	V		
Device Operating Current	72	80	88	mA		
Thermal Resistance (junction to lead)		102		°C/W		

 $Test \ Conditions: \ V_S=8V, \ I_D=80 \ mA \ Typ., \ OIP_3 \ Tone \ Spacing=1 \ MHz, \ P_{OUT} \ per \ tone=0 \ dBm, \ R_{BIAS}=39 \Omega, \ T_L=25 \ ^{\circ}C, \ Z_S=Z_L=50 \Omega$ 

# **SBA-4086(Z)**



#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Device Current (I <sub>D</sub> )	130	mA
Device Voltage (V <sub>D</sub> )	6	V
RF Input Power	+17	dBm
Junction Temp (T <sub>J</sub> )	+150	°C
Operating Temp Range (T <sub>L</sub> )	-40 to +85	°C
Storage Temp	+150	°C
Operating Dissipated Power	0.65	W

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:  $I_DV_D \! < \! (T_J \! - \! T_L) / R_{TH}, j \! - \! l \text{ and } T_L \! = \! T_{LEAD}$ 



#### Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

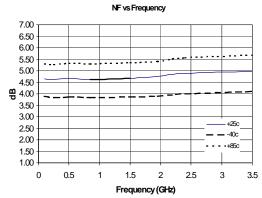
RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

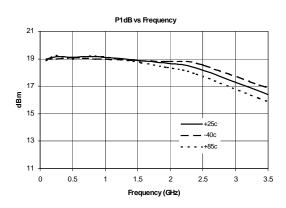
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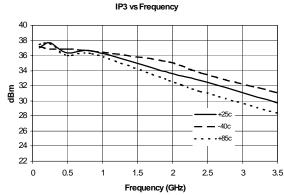
#### Typical Performance at Key Operating Frequencies

Parameter	Unit	100MHz	500 MHz	850MHz	1950MHz	2400 MHz	3500 MHz
Small Signal Gain	dB	15.2	15.0	14.8	14.2	12.4	12.1
Output Third Order Intercept Point	dBm	37.1	36.3	36.5	33.5	32.7	29.7
Output Power at 1dB Compression	dBm	19.0	19.1	19.1	19.0	18.3	16.4
Input Return Loss	dB	36	28	25	21	19.7	17
Output Return Loss	dB	21	21	21.0	20.5	19.6	20.2
Reverse Isolation	dB	18	18	18	18	19	20
Noise Figure	dB	4.7	4.7	4.6	4.8	4.9	5.0

 $\label{eq:conditions: V_S=8V, I_D=80 mA Typ., OIP_3 Tone Spacing=1 MHz, P_{OUT} per tone=0 dBm, R_{BIAS}=39 \Omega, T_L=25 ^{\circ}\text{C}, Z_S=Z_L=50 \Omega ) } \\$ 

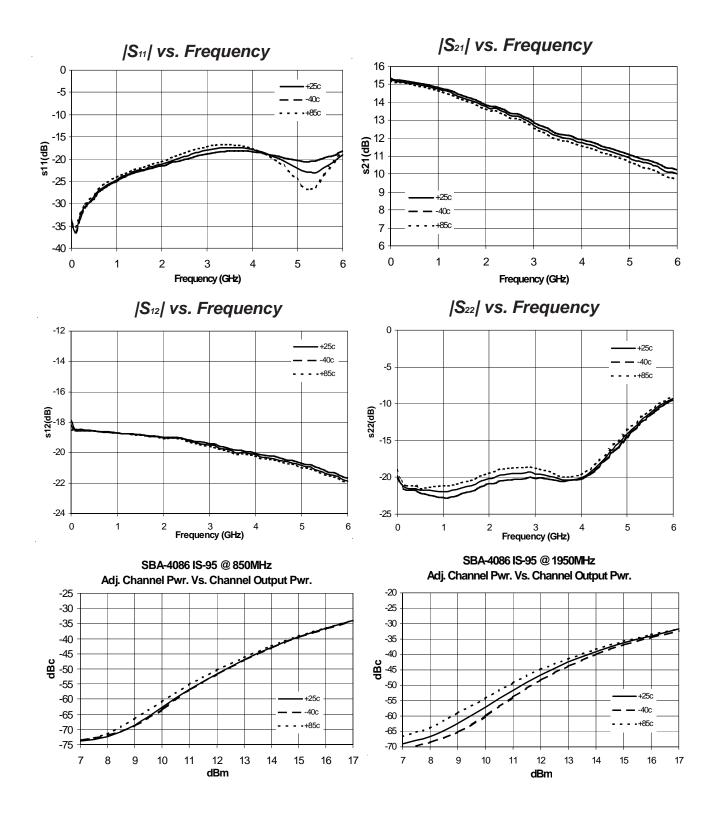






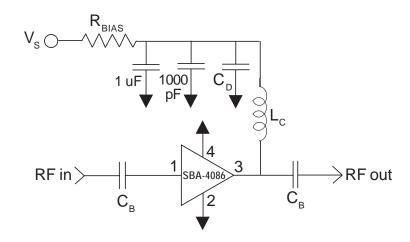




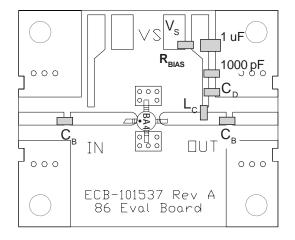




## **Basic Application Circuit**



## **Evaluation Board Layout**



#### Mounting Instructions:

- 1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
- 2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31mil thick FR-4 board with 1 ounce copper on both sides.

#### **Application Circuit Element Values**

Reference Designator	500MHz	850 MHz	1950 MHz	2400 MHz	3500 MHz		
$C_B$	220pF	100 pF	68pF	56pF	39 pF		
C <sub>D</sub>	100pF	68 pF	22pF	22 pF	15 pF		
L <sub>C</sub>	68nH	33 nH	22nH	18nH	15 nH		

### Recommended Bias Resistor Values for $I_D = 80 \text{ mA}$ , $R_{BIAS} = (V_S - V_D) / I_D$

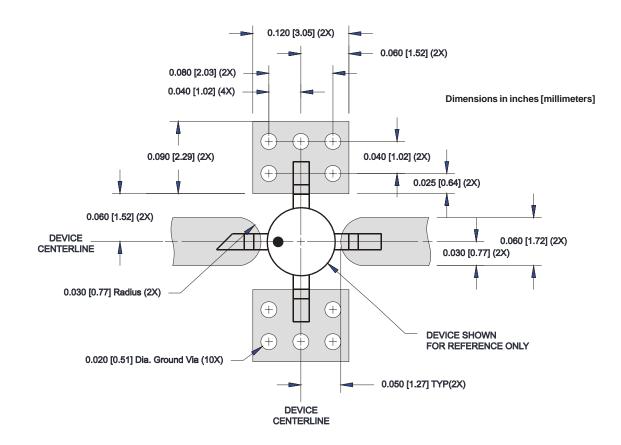
Supply Voltage (V <sub>S</sub> )	7.5 V	8V	10V	12V
R <sub>BIAS</sub>	33Ω	39Ω	68Ω	$91\Omega$

Note:  $\ensuremath{\mathsf{R}_{\mathsf{BIAS}}}$  provides DC bias stability over temperature.



Pin	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.
3	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC-blocking capacitor is necessary for proper operation.

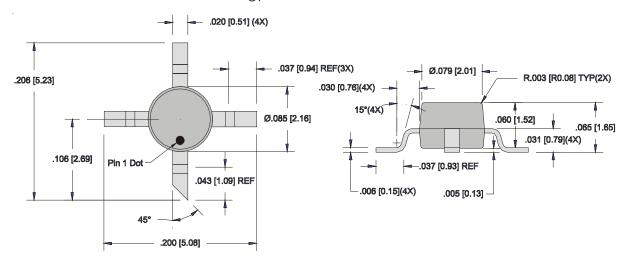
## **PCB Pad Layout**



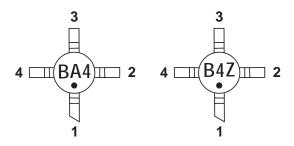


## **Package Drawing**

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.



### **Part Identification**



The part will be marked with a "BA4" or "B42" designator on the top surface of the package.

## **Ordering Information**

Part Number	Reel Size	Devices/Reel
SBA-4086	7"	1000
SBA-4086Z	7"	1000